

Correspondence table of process code and process name

Process code	Process name
TN16FFC	TSMC 16 nm CMOS LOGIC FinFET Compact (Shrink) LL ELK Cu 1P13M 0.8&1.8V
TN28HPCplu	TSMC 28 nm CMOS RF High Performance Compact Mobile Computing Plus ELK Cu 1P10M 0.9&1.8V
AISOC	TSMC 28 nm CMOS LOGIC High Performance Mobile Computing ELK Cu 1P8M 0.9&1.8V
TN40G	TSMC 45 nm CMOS LOGIC General Purpose Superb (40G) ELK Cu 1P10M 0.9/2.5V
TN90GUTM TN90GUTM-E	TSMC 90 nm CMOS Mixed Signal MS General Purpose Standard Process LowK Cu 1P9M 1.0&3.3V (With UTM)
T18 T18-E	TSMC 0.18 UM CMOS Mixed Signal RF General Purpose MiM FSG Al 1P6M 1.8&3.3V
SiGe18 SiGe18-E	TSMC 0.18 UM BICMOS Mixed Signal SiGe General Purpose Standard Process FSG Al 3P6M 1.8&3.3V
T18HVG2	TSMC 0.18UM CMOS HIGH VOLTAGE MIXED SIGNAL BASED GENERATION II BCD 1P6M SALICIDE AL_FSG 1.8/5/6/7/8/12/16/20/24/29/36/45/55/65/70V/VG1.8/5V AND 5/6/7/8/12/16/20/24/29/36/45/55/65/70V/VG5V
T50GaN	TSMC 0.50 UM DISCRETE DEVICE GAN WBG USG AL0P3M HKMG 650V
D35 D35-E	TSMC 0.35 UM Mixed-Signal 2P4M Polycide 3.3/5V
Multi-option- MEMS (Applicable for D35)	TSMC 0.35 UM CMOS Process and APM MEMS Process wi/wo Gold
U18	UMC 0.18 UM Mixed-Mode and RFCMOS 1.8V/3.3V 1P6M Metal Metal Capacitor Process
U18MEMS (Applicable for U18)	UMC 0.18 UM CMOS Process and MEMS Process
P15	WIN 0.15 UM PHEMT
GaN12	WIN 0.12um RF High Power GaN-on-SiC HEMT Technology
GaN25	WIN 0.25um GaN/SiC HEMT Power Device Technology

GIPD	General Purpose Integrated Passive Device (IPD) Process
IMEC-SiPh (iSiPP50G)	imec-ePIXfab SiPhotonics: iSiPP50G
IMEC-SiPh (Passives+)	imec-ePIXfab SiPhotonics: passives+
WIPD	WIN Integrated Passive Device
ADFP	Academic Design Foster Package
C18	TSRI 0.18um 1.8V/3.3V 1P6M Virtual Mixed Mode CMOS Process